#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Brian S. Doyle, et al.,

Serial No.

10/045,376

Filed:

November 9, 2001

For:

Methodology for Control of Short

Channel Effects in MOS Transistors

Group Art:

Not Yet Assigned

Examiner:

Not Yet Assigned

Commissioner of Patents Washington, D.C. 20231

SUBMISSION OF INVENTION DISCLOSURE STATEMENT AND REFERENCES

Dear Sir:

The attached Invention Disclosure Statement and accompanying references are hereby submitted for consideration by the Examiner. These were previously submitted but were apparently never placed in the file. Attached is a photocopy of the return postcard showing that the IDS was previously received by you.

No fee is believed due with this submission. In this is incorrect, please charge any insufficiency or credit any overpayment to Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY SOLOKOFF TAYLOR & ZAFMAN LLP

Date: 4-22-0ユ

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BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LOS ANGELES

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# **Application Number** 10/045,376 **TRANSMITTAL** Filing Date 11-09-2001

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(to be used for all correspondence aft	er initial filing)	Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
Total Number of Pages in This Subn	nission	Attorney Docket Number	42390P5768D
	ENCL	OSURES (check	all that apply)
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Filing Date	11-09-2001	
First Named Invent r	Brian S. Doyle, et al.	
Gr up Art Unit	Not Yet Assigned	
Examiner Name	Not Yet Assigned	
Attorney Docket Number	42390P5768D	

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		D.M. FOLLSTAEDT, S.M. MYERS, G.A. PETERSEN & J.W. MEDERNACH; Cavity Formation and Impurity Gettering in He-Implanted Si; Journal of Electronic Materials, Vol. 25, No. 1, 1996; pp.151-164.	
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